

N-Channel MOSFETs (>500V...900V); Package: PG-TO247-3; VDS (max): 600.0 V;
 Package: TO-247; RDS(ON) @ TJ=25°C VGS=10: 75.0 mOhm; ID(max) @ TC=25°C:
 39.0 A; IDpuls (max): 130.0 A; MOSFET COOL MOS N-CH 600V 0.075Ohms

Manufacturers	Infineon Technologies Corporation
Package/Case	TO-247
Product Type	Transistors
RoHS	Rohs
Lifecycle	



Images are for reference only

Please submit RFQ for IPW60R075CP or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

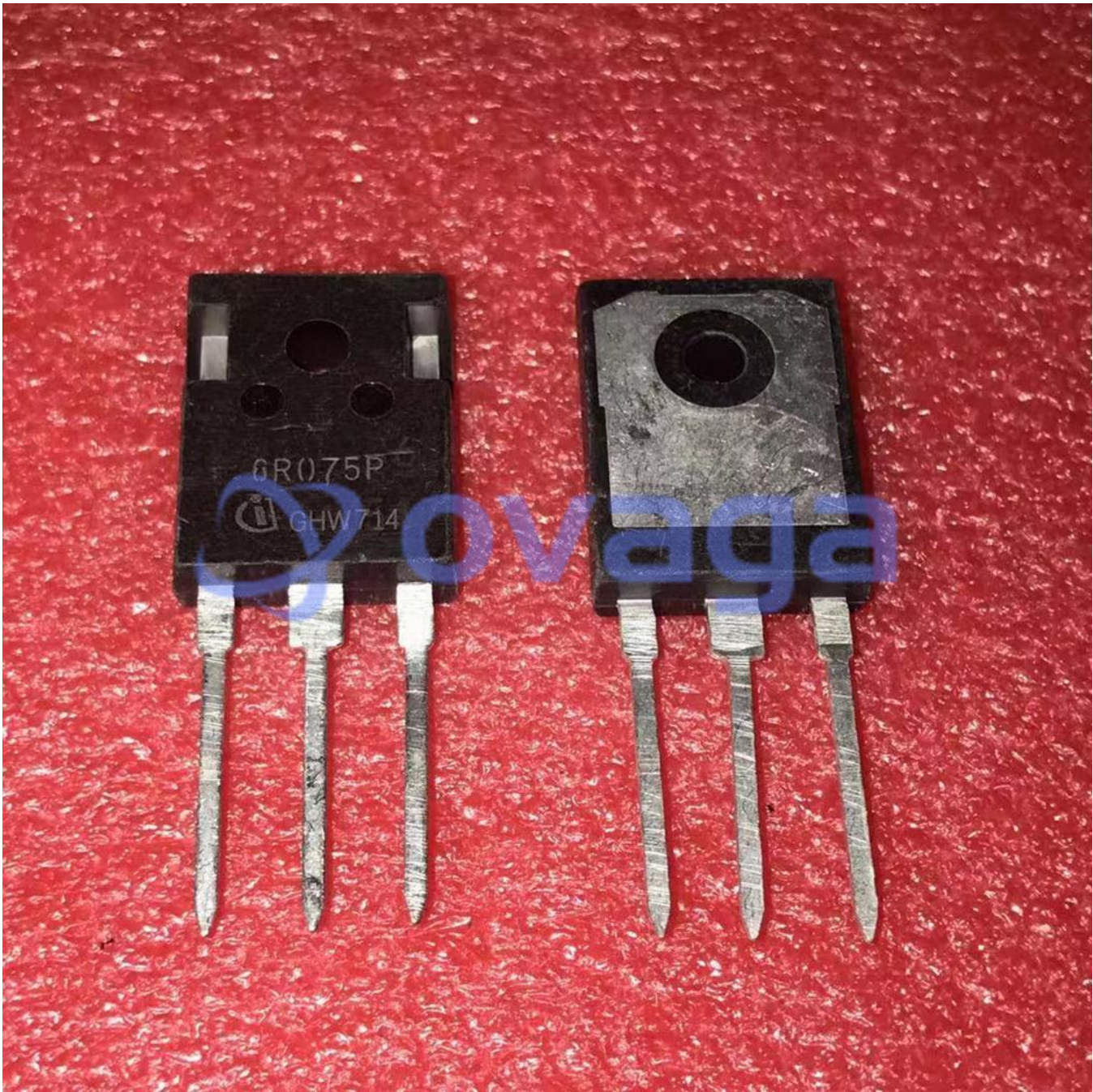
IPW60R075CP is a type of power MOSFET (Metal-Oxide-Semiconductor Field-Effect Transistor) manufactured by Infineon Technologies.

Features

- VDS (Drain-to-Source Voltage): 75V
- ID (Continuous Drain Current): 52A
- RDS(on) (On-Resistance): 6.5mΩ
- Fast switching speed
- Low gate charge
- Low reverse recovery charge
- RoHS compliant

Application

- Switching power supplies
- DC-DC converters
- Motor drives
- Lighting applications
- Solar inverters
- Class-D audio amplifiers



Related Products



[IPP60R070CFD7](#)

Infineon Technologies Corporation
TO-220-3



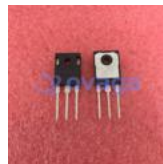
[IPB180N06S4-H1](#)

Infineon Technologies Corporation
PG-TO263-7-3



[IPG20N04S4-12](#)

Infineon Technologies Corporation
TDSON-8



[IPW65R080CFD](#)

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TO-247



[IPD25N06S4L-30](#)

Infineon Technologies Corporation
PG-TO252-3



[IPD180N10N3G](#)

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TO-252



[IPP60R074C6](#)

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TO-220-3



[IPD70R1K4P7S](#)

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TO252-3